

Substitute for form 1449A/B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	NOT YET ASSIGNED 10/527 313
				Filing Date	March 9, 2005
				First Named Inventor	Michael J. Evans
				Art Unit	2823
				Examiner Name	Not Yet Assigned Coleman
				Attorney Docket Number	M0025.0322/P322
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number: Number-Kind Code ² (if known)	Publication Date MM-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
WCI	AA	4,863,877	09-1989	Fan et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
WCI		WO 01/86699-A2	11-2001	Board of Trustees of the Leeland Stanford Junior University		

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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
WCI	CA	Coutaz et al., "Be-doped low-temperature grown GaAs for ultrafast optoelectronic devices and applications," <i>Semiconducting and Insulating Materials Conference 2000</i> , pp. 89 to 96 (2000).			
WCI	CB	Lin & Pan, "Near-Bandgap Ultrafast Optical Responses of Furnace Annealed Arsenic-ion Implanted GaAs," <i>Lasers and Electro-optics Soc. Annual Meeting, Conf. Proceedings IEEE</i> , Vol. 2, pp. 531-32 (Nov. 10-13, 1997).			
WCI	CC	Tan et al., "Ion-Implanted GaAs for subpicosecond applications," <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , Vol. 2, No. 3, pp. 636-642 (Sept. 1996).			

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